

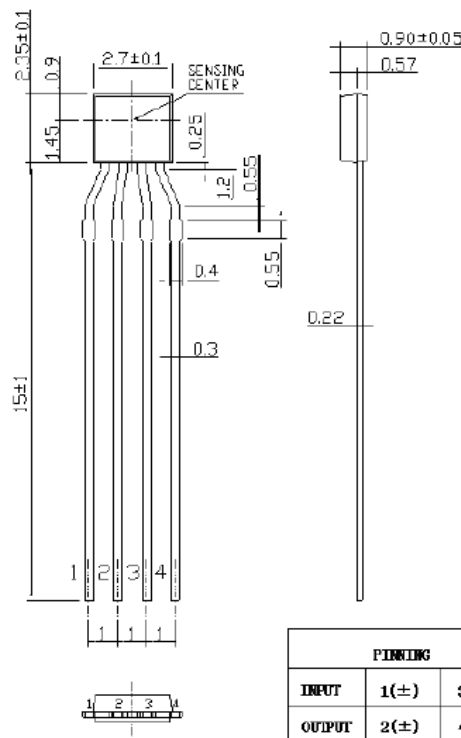
MW921 InSb Hall Element

Ultra High-sensitivity InSb Hall element

Thin-type SIP Package

Shipped in Bulk by Pack (500Pcs devices per pack)

Dimensional Drawing (Unit MM)



Absolute Maximum Rating

Operating Temperature Range $-40^{\circ}\text{C} \sim 110^{\circ}\text{C}$
 Storage Temperature Range $-40^{\circ}\text{C} \sim 125^{\circ}\text{C}$
 Maximum Input Current I_{cmax} [mA] 10mA

Electrical Characteristic (RT=25°C)

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JZWI-DS-010 Version 1.4

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Table 1. Electrical Characteristics of MW921

Item	Symbol	Test Condi.	Min.	Typ.	Max.	Unit
Hall Voltage	V_H	$B = 50\text{mT}, I_C = 1\text{V}$ $T_a = \text{RT}$	168		320	mV
Input Resistance	R_{in}	$B = 0\text{mT}, I_C = 0.1\text{mA}$ $T_a = \text{RT}$	240		550	Ω
Output Resistance	R_{out}	$B = 0\text{mT}, I_C = 0.1\text{mA}$ $T_a = \text{RT}$	240		550	Ω
Offset Voltage	V_{os}	$B = 0\text{mT}, I_C = 1\text{V}$ $T_a = \text{RT}$	-7		+7	mV
Temp. Coeffi. of V_H	$ \alpha V_H $	$B = 50\text{mT}, I_C = 1\text{mA}$, $T_a = 0^\circ\text{C} \sim 40^\circ\text{C}$		1.8		%/ $^\circ\text{C}$
Temp. Coeffi. of R_{in}	αR_{in}	$B = 50\text{mT}, I_C = 5\text{mA}$, $T_a = 0^\circ\text{C} \sim 40^\circ\text{C}$		-1.8		%/ $^\circ\text{C}$
Dielectric strength		100V D.C	1.0			M Ω

- $V_H = V_{H-M} - V_{os}$ in which V_{H-M} is the Output Hall Voltage, V_H is the Hall Voltage and V_{os} is the offset Voltage under the identical electrical stimuli.
- $$\alpha V_H = \frac{1}{V_H(T_1)} \times \frac{V_H(T_3) - V_H(T_2)}{(T_3 - T_2)} \times 100$$
- $$\alpha R_{in} = \frac{1}{R_{in}(T_1)} \times \frac{R_{in}(T_3) - R_{in}(T_2)}{(T_3 - T_2)} \times 100 \quad T_1 = 20^\circ\text{C}, T_2 = 0^\circ\text{C}, T_3 = 40^\circ\text{C}$$

Classification of Output Hall Voltage (V_H)

Table 2. Classification of Hall Voltage

Rank	V_H [mV]	Conditions
C	168 ~ 204	B=50mT, $V_C=1V$
D	196 ~ 236	
E	228 ~ 274	
F	266 ~ 320	

Characteristic Curves

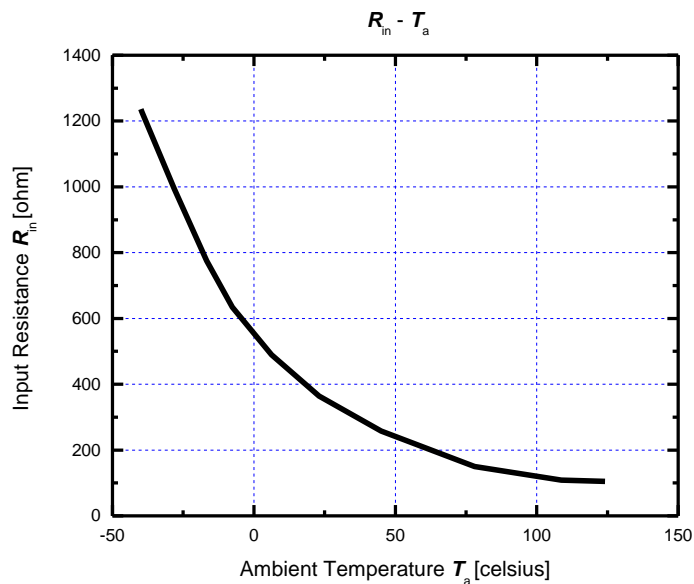


Figure 1. Input resistance R_{in} as a function of ambient temperature T_a .

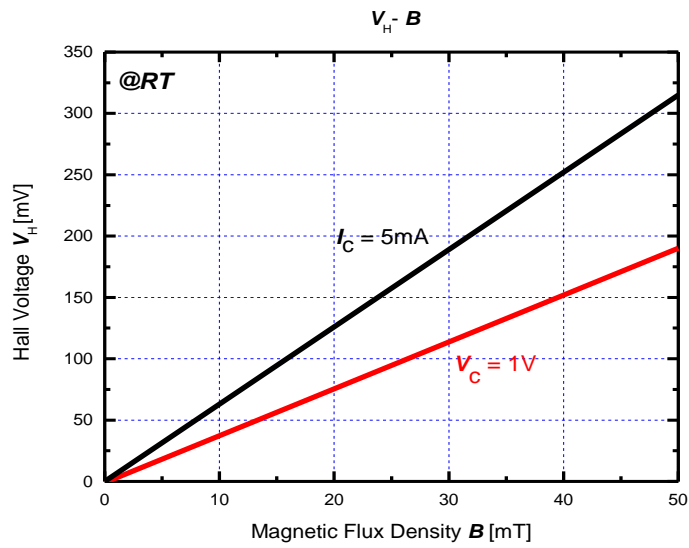


Figure 2. Hall voltage V_H as a function of magnetic flux density B .

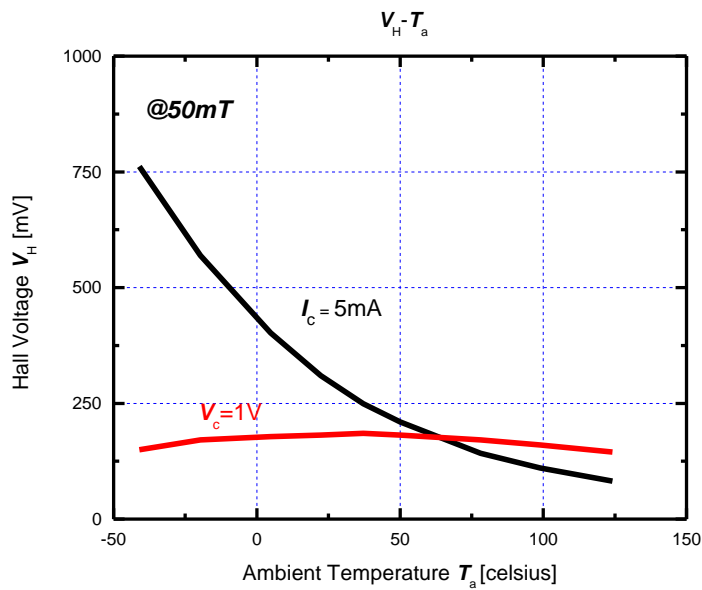


Figure 3. Hall voltage V_H as a function of ambient temperature T_a .

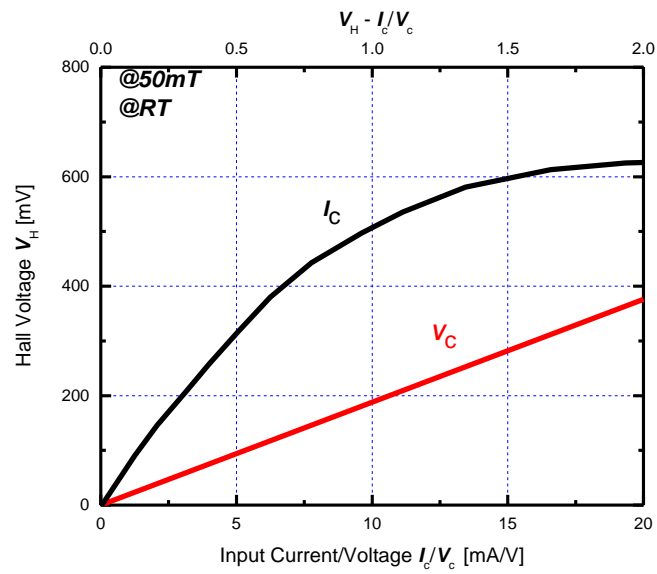


Figure 4. Hall voltage V_H as a function of electrical stimuli I_c/V_c .

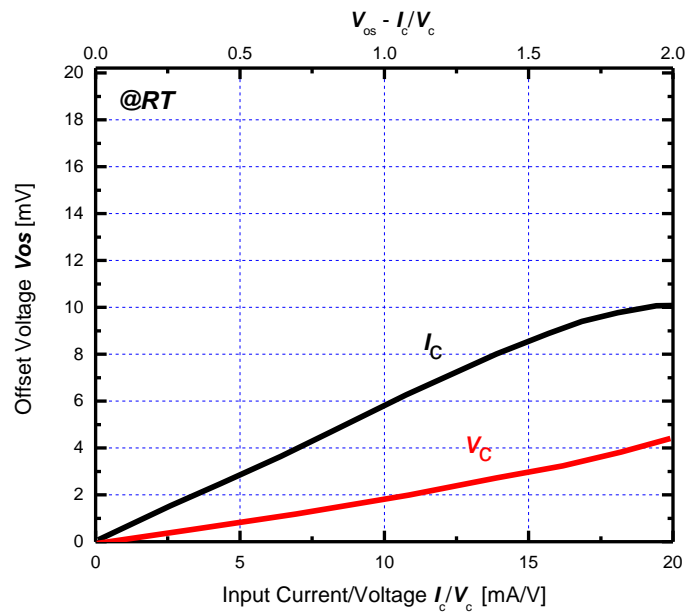


Figure 5. Offset voltage V_{os} as a function of electrical stimuli I_c/V_c .

Precautions for ESD

This product is the device that is sensitive to ESD (Electrostatic Discharge). Handling Hall Elements with the ESD-Caution mark under the environment in which

- Static electrical charge is unlikely to arise. (Ex; Relative Humidity; over 40%RH).
- Wearing the antistatic suit and wristband when handling the devices.
- Implementing measures against ESD as for containers that directly touch the devices.

Precautions for Storage

- Products should be stored at an appropriate temperature and humidity (5 to 35°C, 40 to 60%RH) after the unsealing of MBB. **Using self-sealer is highly recommended.** Keeping products away from chlorine and corrosive gas.
- **For storage longer than 2 years**, it is recommended to store in nitrogen atmosphere with MBB sealed. Oxygen and H₂O of atmosphere oxidizes leads of products and lead solder ability get worse.

Precautions for Safety

- Do not alter the form of this product into a gas, powder or liquid through burning, crushing or chemical processing.
- Observe laws and company regulations when discarding this product.